

Title (en)
CIRCUIT FOR GENERATING A REFERENCE VOLTAGE

Title (de)
SCHALTKREIS ZUR ERZEUGUNG EINER REFERENZSPANNUNG

Title (fr)
CIRCUIT DE GÉNÉRATION D'UNE TENSION DE RÉFÉRENCE

Publication
EP 3176669 A1 20170607 (FR)

Application
EP 16200987 A 20161128

Priority
FR 1561551 A 20151130

Abstract (en)
[origin: US2017153659A1] An FDSOI reference voltage generation circuit, including a CTAT current generation circuit; a PTAT-type voltage generation circuit including a first branch including first and second series-connected transistors, the front surface gates of the first and second transistors being connected to the conduction node of the second transistor opposite to the first transistor; a third diode-assembled transistor having a conduction node connected to an output node of the PTAT voltage generation circuit and having its other conduction node forming a reference voltage supply node; and a current mirror; wherein the first and second transistors are of LVT type and the third transistor is of RVT type.

Abstract (fr)
L'invention concerne un circuit FDSOI de génération d'une tension de référence (V REF), comportant : un circuit (101) de génération d'un courant CTAT (I) ; un circuit (103) de génération d'une tension PTAT (V), comportant une première branche comportant des premier (N4) et deuxième (N5) transistors en série, les grilles de face avant des premier (N4) et deuxième (N5) transistors étant connectées au noeud de conduction du deuxième (N5) transistor opposé au premier transistor (N4) ; un troisième transistor (N8) monté en diode dont un noeud de conduction est connecté à un noeud de sortie du circuit de génération de la tension PTAT et dont l'autre noeud de conduction constitue un noeud de fourniture de la tension de référence (V REF) ; et un miroir de courant (P2, P3, P5), dans lequel les premier (N4) et deuxième (N5) transistors sont de type LVT, et le troisième transistor (N8) est de type RVT.

IPC 8 full level
G05F 3/24 (2006.01)

CPC (source: EP US)
G05F 3/242 (2013.01 - EP US); **G05F 3/267** (2013.01 - EP US)

Citation (applicant)
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